

ABSTRACT

In a semiconductor photodetector 1 according to the present invention, flat surfaces of three steps with different heights are formed in a top surface portion of a semi-insulating GaAs substrate 2. An n-type GaAs layer 3, an i-type GaAs layer 4, and a p-type GaAs layer 5 are successively deposited on the lower step surface formed in a central region of the semi-insulating GaAs substrate 2. Furthermore, a p-side ohmic electrode 6 is provided astride and above a flat surface formed by the p-type GaAs layer 5 and the upper step surface of the semi-insulating GaAs substrate 2, and an n-side ohmic electrode 7 is provided astride and above a flat surface formed by the n-type GaAs layer 3 and the middle step surface of the semi-insulating GaAs substrate 2.